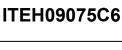
Document Number: ITEH09075C6 Preliminary Datasheet V1.0

25W,12.5V High Power RF LDMOS FETs

Description

The ITEH09075C6 is a 25-watt, highly rugged, unmatched LDMOS FET, designed for commercial and industrial applications at frequencies up to 1GHz. It can be used in linear or saturated power amplifier, for CW and pulsed signal, and any modulation format. It is also featured by its lower cost of plastic open cavity for surface mount on PCB through vias

Typical LMR UHF CW Performance (On Innogration fixture with device soldered).





	Condition: V_{ds} = 12.5V, I_{dq} =300mA, V_{gs} =2.70V					
Freq (MHz)	P1(dBm)	P1 Gain (dB)	P3dB(dBm)	P3dB(W)	EFF (%)	
400	43.60	19.02	44.69	29.5	48.3	
410	44.27	18.86	45.31	33.9	51.6	
420	44.68	19.29	45.73	37.4	54.2	
430	45.14	20.09	46.11	40.8	57.4	
440	45.03	20.82	46.11	40.8	58.5	
450	44.31	20.97	45.62	36.5	56.8	
460	43.49	20.17	45.21	33.2	53.9	
470	42.59	19.94	45.21	33.2	54.7	
480	43.06	19.38	44.56	28.6	55.5	

Typical 900MHz CW Performance (On Innogration fixture with device soldered).
 Vds= 12.5V, Idq=100mA(Vgs=3.30V)

Freq	P1dB	P1dB	P1dB Eff	P1dB Gain	P3dB	P3dB	P3dB Eff
(MHz)	(dBm)	(W)	%	dB	(dBm)	(W)	%
902	42.74	18.8	58.1	18.57	44.38	27.4	66.5
915	42.46	17.6	61.8	18.58	44.02	25.2	69.9
928	42.01	15.9	63.8	18.31	43.37	21.7	69.7

Features

- High Efficiency and Linear Gain Operations
- Integrated ESD Protection
- Excellent thermal stability, low HCI drift
- Large Positive and Negative Gate/Source Voltage Range for Improved Class C Operation
- Pb-free, RoHS-compliant

Suitable Applications

- VHF/UHF Land mobile radio (LMR)
- RF Energy application at ISM bands

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
DrainSource Voltage	$V_{\scriptscriptstyle DSS}$	+70	Vdc
GateSource Voltage	$V_{\sf GS}$	-10 to +10	Vdc



Innogration (Suzhou) Co., Ltd.

Document Number: ITEH09075C6 Preliminary Datasheet V1.0

Operating Voltage	V_{DD}	+28	Vdc
Storage Temperature Range	Tstg	-65 to +150	°C
Case Operating Temperature	Tc	+150	°C
Operating Junction Temperature	TJ	+225	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case	Do 10	0.9	°C/W
T _C = 85°C, T _J =200°C, DC test	R⊕JC	0.8	-0/00

Table 3. ESD Protection Characteristics

Test Methodology	Class
Human Body Model (per JESD22A114)	Class 1B

Table 4. Electrical Characteristics (TA = 25 °C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
DC Characteristics					
Drain-Source Voltage	.,		70		٧
V _{GS} =0, I _{DS} =100uA	V _{(BR)DSS}				V
Zero Gate Voltage Drain Leakage Current				1	^
$(V_{DS} = 13.6V, V_{GS} = 0 V)$	I _{DSS}			ı	μΑ
GateSource Leakage Current				1	^
$(V_{GS} = 9 \text{ V}, V_{DS} = 0 \text{ V})$	Igss			I	μΑ
Gate Threshold Voltage	V _{GS} (th)		2		V
$(V_{DS} = 12.5V, I_D = 600 \mu A)$	V GS(III)		2		V
Gate Quiescent Voltage	$V_{GS(Q)}$		2.7		V
$(V_{DD} = 12.5V, I_D = 300mA, Measured in Functional Test)$	V GS(Q)		2.1		V

 $\textbf{Load Mismatch (In Innogration Test Fixture, 50 ohm system):} \quad V_{DD} = 12.5 \text{Vdc}, \ I_{DQ} = 300 \ \text{mA}, \ f = 1000 \ \text{MHz}$

VSWR 10:1 at 25W pulse CW Output Power	No Device Degradation
--	-----------------------

Figure 1:Pin Definition(Top View)



Pin No.	Symbol	Description
1-7,12,13,18-25,30,31,36	GND	DC/RF Ground
8,9,10,11,14,15,16,17	Vgs/RF In	Vgs and RF input
26,27,28,29,32,33,34,35	Vds/RF out	Vds and RF output
Package Base	GND	DC/RF Ground.



400-480MHz broadband Reference Circuit of Test Fixture Assembly Diagram

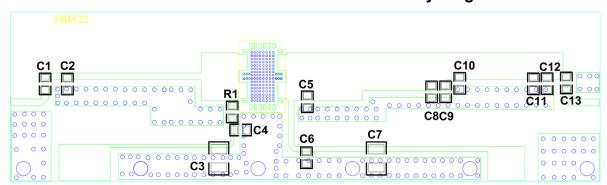


Figure 2. Test Circuit Component Layout

Table 5. Test Circuit Component Designations and Values

Component	Description	Suggestion
C1,C4,C6,C13	100pF	MQ300805C
C2	22pF	ATC600S
C3,C7	10uF	TDK1206
C5	5.1pF	ATC600S
C8	8.2pF	ATC600S
C9,C10	10pF	ATC600S
C11	4.7pF	ATC600S
C12	12pF	ATC600S
R1	10 Ω	MQ300603C
PCB	20Mil	Rogers4350

TYPICAL CHARACTERISTICS

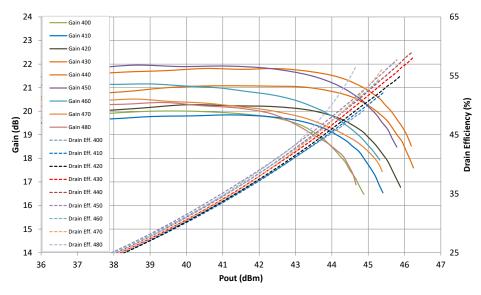


Figure 3. Gain and Efficiency as function of CW Power Output



900MHz

Reference Circuit of Test Fixture Assembly Diagram

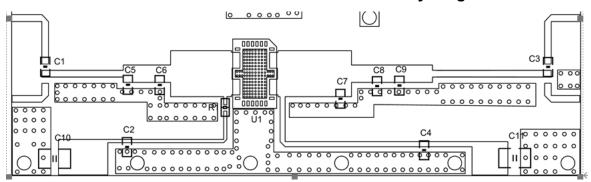
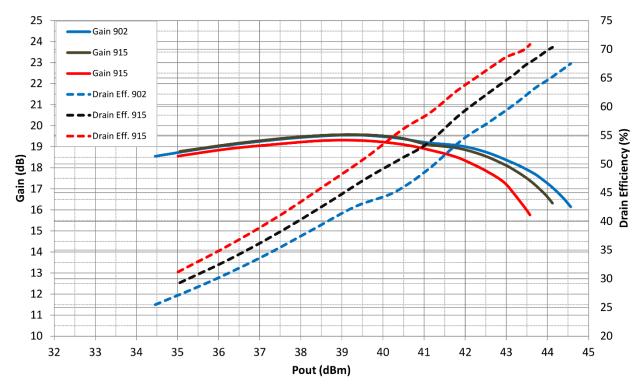


Figure 5. Test Circuit Component Layout

Table 6. Test Circuit Component Designations and Values

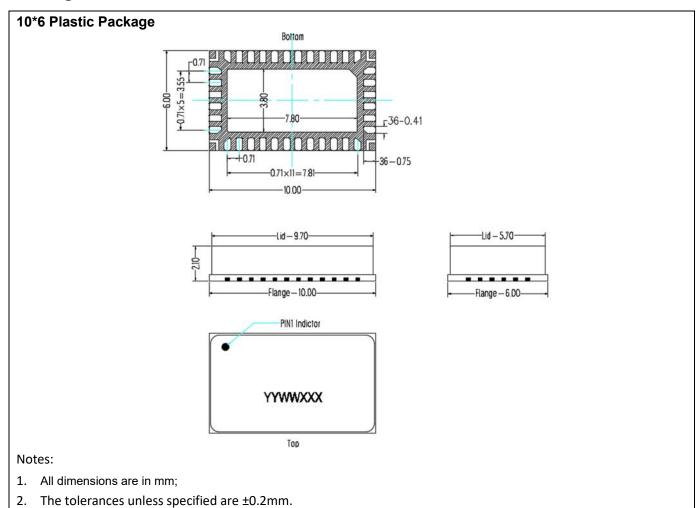
Reference	Footprint	Value	Quantity
C2, C3, C4	0603	47pF/250V	3
C1, C5	0603	10pF/250V	2
C6, C7, C8	0603	5.6pF/250V	3
C9	0603	6.8pF/250V	1
C10, C11	1210	10uF/100V	2
R1	0603	10R	1
U1		ITEH09075C6	1

Typical performance



Document Number: ITEH09075C6 Preliminary Datasheet V1.0

Package Dimensions



Revision history

Table 6. Document revision history

Date	Revision	Description
2025/1/14	Rev 1.0	as replacement of ITEH09070C6

Application data based on HJ-24-20/ZBB-25-05

Disclaimers

Specifications are subject to change without notice. Innogration believes the information contained within this data sheet to be accurate and reliable. However, no responsibility is assumed by Innogration for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Innogration . Innogration makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose. "Typical" parameters are the average values expected by Innogration in large quantities and are provided for information purposes only. These values can and do vary in different applications and actual performance can vary over time. All operating parameters should be validated by customer's technical experts for each application. Innogration products are not designed, intended or authorized for use as components in applications intended for surgical implant into the body or to support or sustain life, in applications in which the failure of the Innogration product could result in personal injury or death or in applications for planning, construction, maintenance or direct operation of a nuclear facility. For any concerns or questions related to terms or conditions, pls check with Innogration and authorized distributors Copyright © by Innogration (Suzhou) Co.,Ltd.